



# BYV10ED-600P

Ultrafast power diode

24 July 2015

Product data sheet

## 1. General description

Enhanced ultrafast power diode in a SOT428 (DPAK) plastic package.

## 2. Features and benefits

- High thermal cycling performance
- Soft recovery characteristic
- Low on-state losses
- Surface-mountable package
- Low thermal resistance
- Enhanced avalanche energy capability

## 3. Applications

- Dual Mode (DCM and CCM) PFC
- Power Factor Correction (PFC) for Interleaved Topology

## 4. Quick reference data

Table 1. Quick reference data

| Symbol                  | Parameter                           | Conditions  |  | Min | Typ | Max | Unit |
|-------------------------|-------------------------------------|---|--|-----|-----|-----|------|
| V <sub>RRM</sub>        | repetitive peak reverse voltage     |   |  | -   | -   | 600 | V    |
| I <sub>F(AV)</sub>      | average forward current             | δ = 0.5 ; T <sub>mb</sub> ≤ 118 °C; Square-wave pulse; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> |  | -   | -   | 10  | A    |
| I <sub>FRM</sub>        | repetitive peak forward current     | δ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 118 °C; Square-wave pulse   |  | -   | -   | 20  | A    |
| I <sub>FSM</sub>        | non-repetitive peak forward current | t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; SIN; <a href="#">Fig. 4</a>   |  | -   | -   | 70  | A    |
|                         |                                     | t <sub>p</sub> = 8.3 ms; T <sub>j(init)</sub> = 25 °C; SIN; <a href="#">Fig. 4</a>  |  | -   | -   | 80  | A    |
| Static characteristics  |                                     |   |  |     |     |     |      |
| V <sub>F</sub>          | forward voltage                     | I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 6</a>   |  | -   | 1.5 | 2   | V    |
|                         |                                     | I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <a href="#">Fig. 6</a>  |  | -   | -   | 1.6 | V    |
| Dynamic characteristics |                                     |   |  |     |     |     |      |
| t <sub>rr</sub>         | reverse recovery time               | I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 50 A/μs; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>      |  | -   | 35  | 50  | ns   |



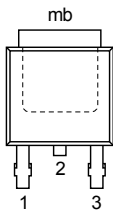
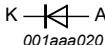
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| Symbol                  | Parameter                       | Conditions   | Min | Typ | Max | Unit |
|-------------------------|---------------------------------|--|-----|-----|-----|------|
|                         |                                 | $I_F = 10\text{ A}$ ; $V_R = 200\text{ V}$ ; $di_F/dt = 200\text{ A}/\mu\text{s}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; Fig. 7  | -   | 50  | -   | ns   |
|                         |                                 | $I_F = 10\text{ A}$ ; $V_R = 200\text{ V}$ ; $di_F/dt = 200\text{ A}/\mu\text{s}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; Fig. 7 | -   | 78  | -   | ns   |
| <b>Avalanche energy</b> |                                 |  |     |     |     |      |
| $E_{AS}$                | non-repetitive avalanche energy | $I_R = 2.6\text{ A}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $L = 15\text{ mH}$                                    | -   | 50  | -   | mJ   |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                         | Simplified outline   | Graphic symbol  |
|-----|--------|-------------------------------------|--|---|
| 1   | n.c.   | not connected                       |  <p><b>DPAK (SOT428)</b></p> |  |
| 2   | K      | cathode[1]                          |  |   |
| 3   | A      | anode                               |  |   |
| mb  | K      | mounting base; connected to cathode |  |   |

[1] It is not possible to connect to pin 2 of the SOT428 package.

## 6. Ordering information

Table 3. Ordering information

| Type number  | Package |   |         |
|--------------|---------|---|---------|
|              | Name    | Description   | Version |
| BYV10ED-600P | DPAK    | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428  |

## 7. Marking

Table 4. Marking codes

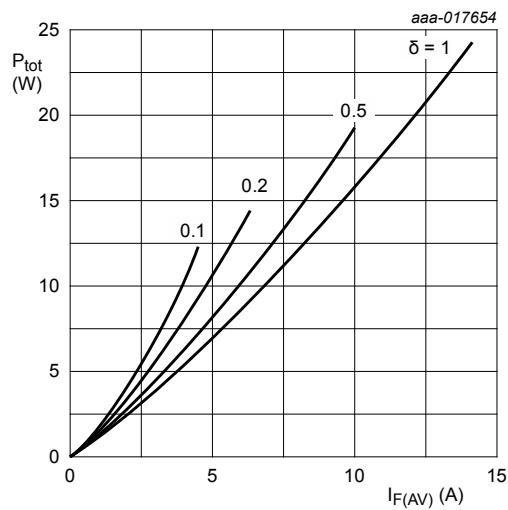
| Type number  | Marking code |
|--------------|--------------|
| BYV10ED-600P | BYV10ED-600P |

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

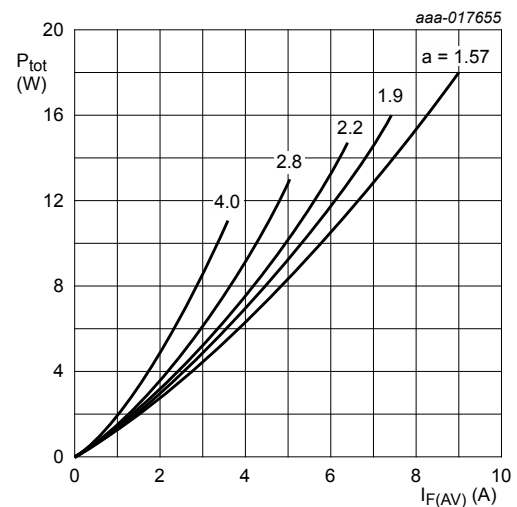
| Symbol      | Parameter                           | Conditions   | Min | Max | Unit             |
|-------------|-------------------------------------|--|-----|-----|------------------|
| $V_{RRM}$   | repetitive peak reverse voltage     |  | -   | 600 | V                |
| $V_{RWM}$   | crest working reverse voltage       |  | -   | 600 | V                |
| $V_R$       | reverse voltage                     | DC   | -   | 600 | V                |
| $I_{F(AV)}$ | average forward current             | $\delta = 0.5$ ; $T_{mb} \leq 118^\circ\text{C}$ ; Square-wave pulse; Fig. 1; Fig. 2; Fig. 3         | -   | 10  | A                |
| $I_{FRM}$   | repetitive peak forward current     | $\delta = 0.5$ ; $t_p = 25\text{ }\mu\text{s}$ ; $T_{mb} \leq 118^\circ\text{C}$ ; Square-wave pulse | -   | 20  | A                |
| $I_{FSM}$   | non-repetitive peak forward current | $t_p = 10\text{ ms}$ ; $T_{j(\text{init})} = 25^\circ\text{C}$ ; SIN; Fig. 4                         | -   | 70  | A                |
|             |                                     | $t_p = 8.3\text{ ms}$ ; $T_{j(\text{init})} = 25^\circ\text{C}$ ; SIN; Fig. 4                        | -   | 80  | A                |
| $T_{stg}$   | storage temperature                 |  | -40 | 175 | $^\circ\text{C}$ |
| $T_j$       | junction temperature                |  | -   | 175 | $^\circ\text{C}$ |



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 1.241\text{ V}; R_s = 0.034\text{ }\Omega$$

**Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values**



$$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$$

$$V_o = 1.241\text{ V}; R_s = 0.034\text{ }\Omega$$

**Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values**

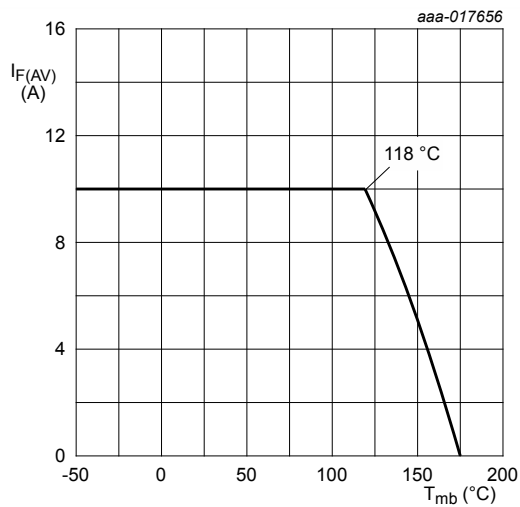


Fig. 3. Forward current as a function of mounting base temperature; maximum values

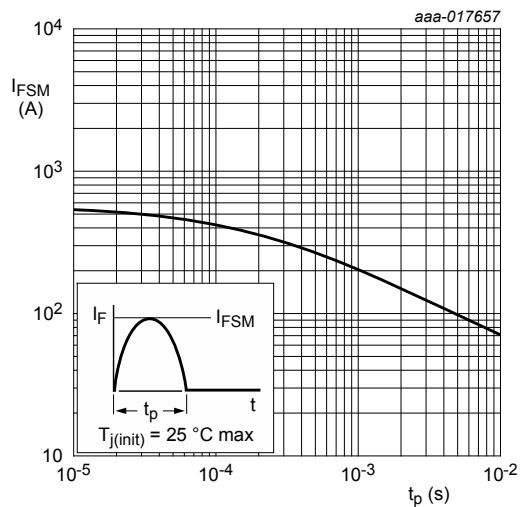


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter  | Conditions                                     |  | Min | Typ | Max | Unit |
|----------------|--|--|--|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base    | With heatsink compound; <a href="#">Fig. 5</a> |  | -   | -   | 3   | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient free air | in free air                                    |  | -   | 50  | -   | K/W  |

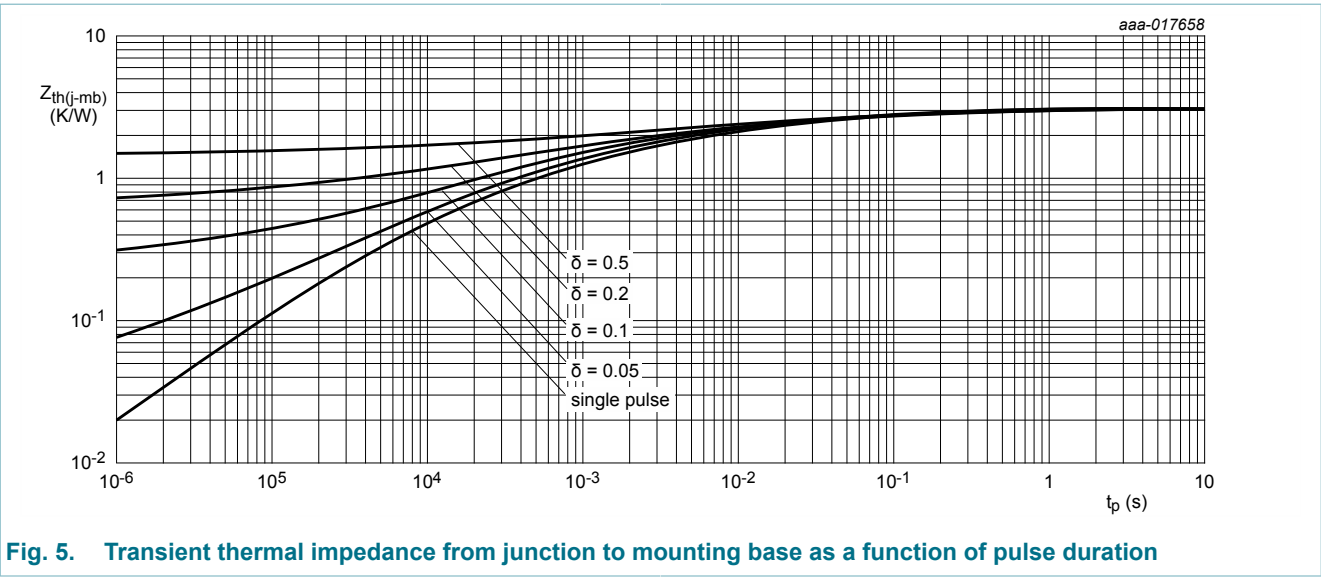
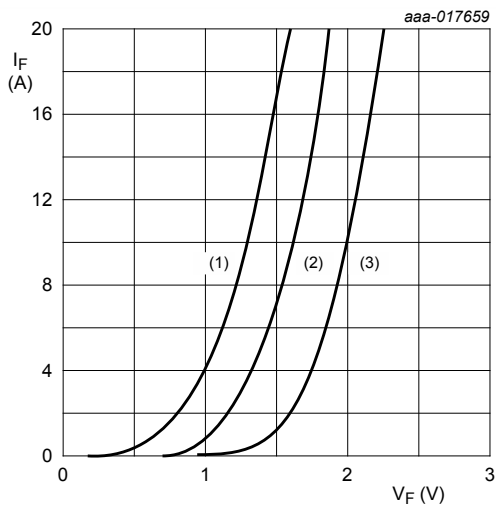


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

| Symbol                  | Parameter                       | Conditions   |  | Min | Typ | Max | Unit |
|-------------------------|---------------------------------|--|--|-----|-----|-----|------|
| Static characteristics  |                                 |  |  |     |     |     |      |
| V <sub>F</sub>          | forward voltage                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 6</a>  |  | -   | 1.5 | 2   | V    |
|                         |                                 | I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <a href="#">Fig. 6</a>   |  | -   | -   | 1.6 | V    |
| I <sub>R</sub>          | reverse current                 | V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C   |  | -   | -   | 10  | μA   |
|                         |                                 | V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C  |  | -   | -   | 500 | μA   |
| Dynamic characteristics |                                 |  |  |     |     |     |      |
| Q <sub>r</sub>          | recovered charge                | I <sub>F</sub> = 10 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>  |  | -   | 123 | -   | nC   |
|                         |                                 | I <sub>F</sub> = 10 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <a href="#">Fig. 7</a> |  | -   | 305 | -   | nC   |
| t <sub>rr</sub>         | reverse recovery time           | I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 50 A/μs; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>     |  | -   | 35  | 50  | ns   |
|                         |                                 | I <sub>F</sub> = 10 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>  |  | -   | 50  | -   | ns   |
|                         |                                 | I <sub>F</sub> = 10 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <a href="#">Fig. 7</a> |  | -   | 78  | -   | ns   |
| I <sub>RM</sub>         | peak reverse recovery current   | I <sub>F</sub> = 10 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>  |  | -   | 4.9 | -   | A    |
|                         |                                 | I <sub>F</sub> = 10 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <a href="#">Fig. 7</a> |  | -   | 7.8 | -   | A    |
| Avalanche energy        |                                 |  |  |     |     |     |      |
| E <sub>AS</sub>         | non-repetitive avalanche energy | I <sub>R</sub> = 2.6 A; T <sub>j(init)</sub> = 25 °C; L = 15 mH  |  | -   | 50  | -   | mJ   |



$V_o = 1.241\text{ V}$ ;  $R_s = 0.034\text{ }\Omega$

- (1)  $T_j = 150\text{ }^\circ\text{C}$ ; typical values
- (2)  $T_j = 150\text{ }^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25\text{ }^\circ\text{C}$ ; maximum values

Fig. 6. Forward current as a function of forward voltage

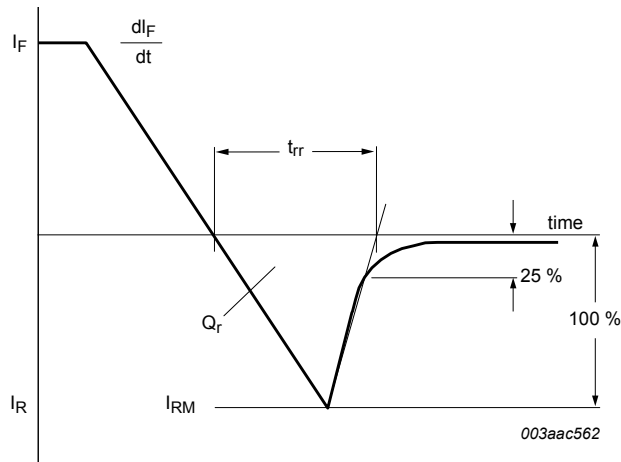
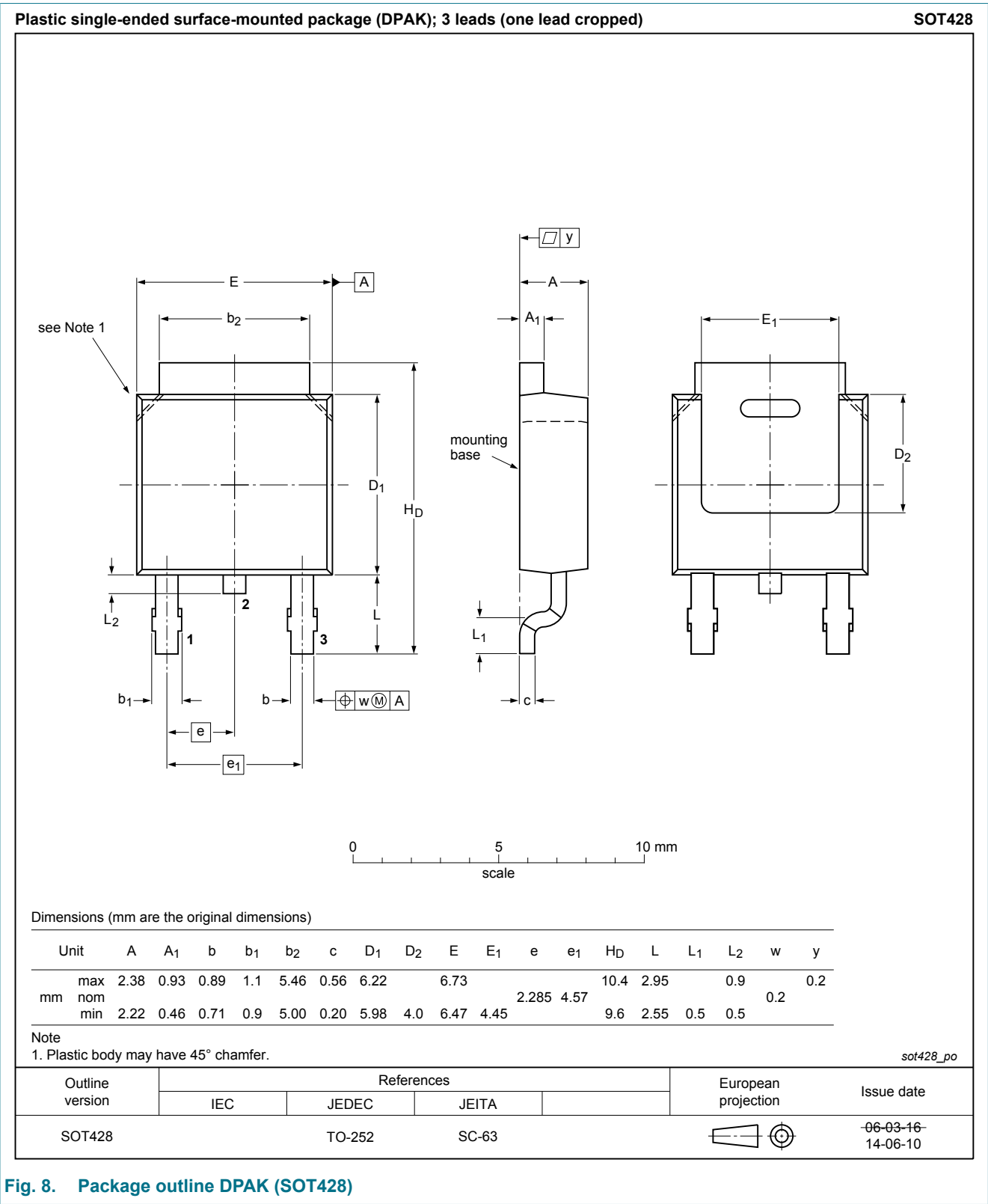


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline





## 12. Legal information

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